

# Waveguide-integrated, plasmonic enhanced graphene photodetectors

**J. E. Muench**<sup>1</sup>, A. Ruocco<sup>1</sup>, V. Miseikis<sup>2,3,4</sup>, M. A. Giambra<sup>2</sup>, D. Zhang<sup>1</sup>, J. Wang<sup>1</sup>, H.F.Y. Watson<sup>1</sup>, G.C. Park<sup>1</sup>, S. Akhavan<sup>1</sup>, V. Sorianello<sup>2</sup>, M. Midrio<sup>5</sup>, C. Coletti<sup>3,4</sup>, M. Romagnoli<sup>2</sup>, A. C. Ferrari<sup>1</sup>, I. Goykhman<sup>6</sup>

<sup>1</sup>Cambridge Graphene Centre, University of Cambridge, 9 JJ Thomson Avenue, Cambridge CB3 0FA, UK

<sup>2</sup>Consorzio Nazionale per le Telecomunicazioni (CNIT), Photonic Networks and Technologies National Laboratory, 56127 Pisa, Italy

<sup>3</sup>Center for Nanotechnology Innovation @ NEST, Istituto Italiano di Tecnologia, 56127 Pisa, Italy

<sup>4</sup>Graphene Labs, Istituto Italiano di Tecnologia, 16163 Genova, Italy

<sup>5</sup>Consorzio Nazionale per le Telecomunicazioni, University of Udine, 33100 Udine, Italy

<sup>6</sup>Micro- and Nanoelectronics Research Center, Technion – Israel Institute of Technology, Technion City, Haifa 320000, Israel

[jem227@cam.ac.uk](mailto:jem227@cam.ac.uk)

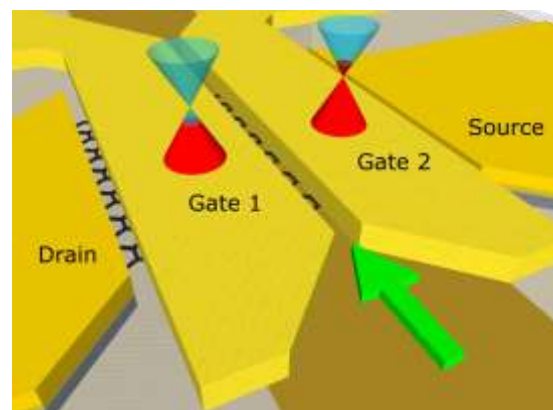
The integration of single-layer graphene (SLG) with Si may improve the performance of key active components required in Data- and Telecoms [1-5]. Waveguide - integrated graphene photodetectors (GPDs) based on the photo-thermoelectric (PTE) effect can directly generate a photovoltage, which could potentially remove the need for transimpedance amplifiers commonly employed in optical receivers, offering a reduction in fabrication cost and power consumption. Here we present a plasmonic enhanced PTE-based GPD integrated with SiN waveguides. Our design employs scalable SLG grown by chemical vapour deposition and relies on two metal gates, centrally aligned to the waveguide, to generate a p-n junction in the SLG and simultaneously support plasmonic guiding in the gap between them (Fig. 1). This leads to enhanced SLG-light interaction, resulting in a steeper electronic temperature gradient across the device. Our GPDs shows an external responsivity up to  $\sim 12\text{V/W}$ , whilst maintaining high-speed operation (up to 40 GHz) and small device footprints ( $< 20\ \mu\text{m}^2$ ),

thus paving the way towards SLG integrated receivers.

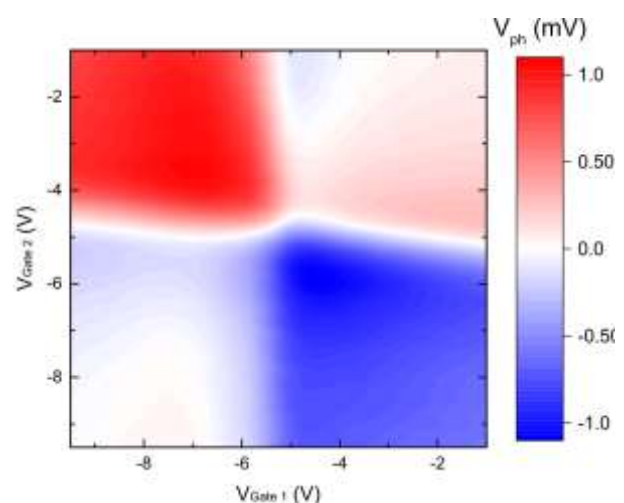
## References

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## Figures



**Figure 1:** Schematic view of the plasmonic enhanced graphene PD



**Figure 2:** Experimental photovoltage map, measured under zero source-drain bias.